

Sensors



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TLE4966L

Revision H	listory: 2009-02	V 2.0
Previous Ve	ersion: V 1.2	
Page	Subjects (major changes since last revision)	
	TLE4966H removed	

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TLE4966L



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High Precision Hall-Effect Switch with Direction Detection

TLE4966L

1 Overview

1.1 Features

- 2.7 V to 24 V supply voltage operation
- · Operation from unregulated power supply
- High sensitivity and high stability of the magnetic switching points
- High resistance to mechanical stress by Active Error Compensation
- Reverse battery protection (-18 V)
- · Superior temperature stability
- Peak temperatures up to 195°C without damage
- Low jitter (typ. 1 μs)
- Digital output signals
- Bipolar version
- Excellent matching between the 2 Hall probes
- Hall plate distance 1.45 mm
- Direction & speed information
- Direction signal switches before the speed signal

1.2 Functional Description

The TLE4966L is an integrated circuit double Hall-effect sensor designed specifically for highly accurate applications. Precise magnetic switching points and high temperature stability are achieved by active compensation circuits and chopper techniques on chip. The IC provides a speed signal at Q2 for every magnetic pole pair and a direction information at Q1, which is provided before the speed signal.

Туре	Package
TLE4966L	PG-SSO-4-1



Overview

1.3 Pin Configuration (top view)

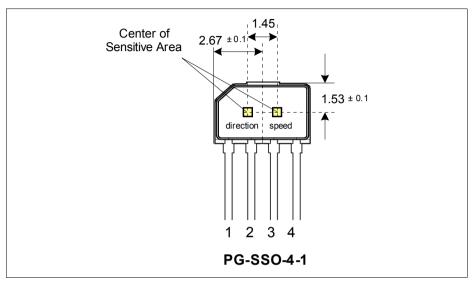


Figure 1 Pin Definition and Center of Sensitive Area

Table 1 Pin Definitions and Functions

Pin No.	Symbol	Function
1	V_{S}	Supply voltage
2	Q1	Direction
3	Q2	Speed
4	GND	Ground



General

2 General

2.1 Block Diagram

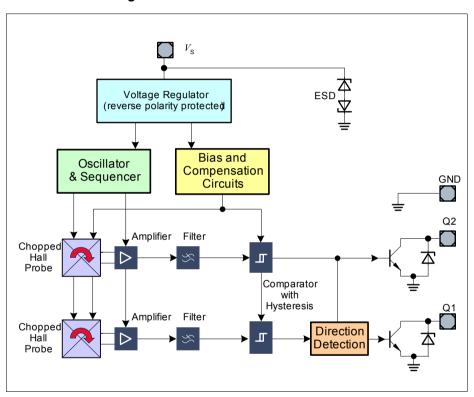


Figure 2 Block Diagram

2.2 Circuit Description

The chopped Double Hall Switch comprises two Hall probes, bias generator, compensation circuits, oscillator, and output transistors.

The bias generator provides currents for the Hall probes and the active circuits. Compensation circuits stabilize the temperature behavior and reduce technology variations.

The Active Error Compensation rejects offsets in signal stages and the influence of mechanical stress to the Hall probes caused by molding and soldering processes and other thermal stresses in the package. This chopper technique together with the threshold generator and the comparator ensures high accurate magnetic switching points.



Maximum Ratings

3 Maximum Ratings

Table 2 Absolute Maximum Ratings $T_i = -40^{\circ}\text{C}$ to 150°C

Parameter	Symbol	Lin	nit Values	Unit	Conditions	
		min.	max.			
Supply voltage	V_{S}	-18 -18 -18	18 24 26	V	for 1 h, $R_{\rm S} \ge 200~\Omega$ for 5 min, $R_{\rm S} \ge 200~\Omega$	
Supply current through protection device	$I_{\mathbb{S}}$	-50	50	mA		
Output voltage	V_{Q}	-0.7 -0.7	18 26	V	for 5 min @ 1.2 kΩ pull up	
Continuous output current	I_{Q}	-50	50	mA		
Junction temperature	T_{j}	- - -	155 165 175 195	°C	for 2000 h (not additive) for 1000 h (not additive) for 168 h (not additive) for 3 x 1 h (additive)	
Storage temperature	T_{S}	-40	150	°C		
Magnetic flux density	В	_	unlimited	mT		

Note: Stresses above those listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 3 ESD Protection 1)

Parameter	Symbol	Limit Values		Limit Values		Unit	Notes
		min.	max.				
ESD voltage	V_{ESD}	-	±4	kV	HBM, R = 1.5 kΩ, C = 100 pF $T_{\rm A}$ = 25°C		

Human Body Model (HBM) tests according to: EOS/ESD Association Standard S5.1-1993 and Mil. Std. 883D method 3015.7



Operating Range

4 Operating Range

Table 4 Operating Range

Parameter	Symbol	L	imit Va	ues	Unit	Conditions	
		min.	typ.	max.			
Supply voltage	V_{S}	2.7	_	18	V		
,		_	_	24		1 h with $R_{\rm S} \ge 200 \ \Omega$	
		_	_	26		for 5 min $R_S \ge 200 \Omega$	
Output voltage	V_{Q}	-0.7	_	18	V		
Junction	$T_{\rm i}$	-40	_	150	°C		
temperature	,	_	_	175		for 168 h	
Output current	I_{Q}	0	_	10	mA		



Electrical and Magnetic Parameters

5 Electrical and Magnetic Parameters

Table 5 Electrical Characteristics 1)

Parameter	Symbol	Limit Values			Unit	Conditions	
		min.	typ.	max.			
Supply current	I_{S}	4	5.2	7	mA	V _S = 2.7 V 18 V	
Reverse current	I_{SR}	0	0.2	1	mA	V _S = -18 V	
Output saturation voltage	V_{QSAT}	_	0.3	0.6	V	$I_{\rm Q}$ = 10 mA	
Output leakage current	I_{QLEAK}	_	0.05	10	μА	for V_Q = 18 V	
Output fall time	t_{f}	_	0.2	1	μs	$R_{\rm L}$ = 1.2 k Ω ; $C_{\rm L}$ < 50 pF	
Output rise time	t_{r}	_	0.2	1	μs	see: Figure 3 on Page 12	
Chopper frequency	$f_{\sf OSC}$	_	320	-	kHz		
Switching frequency	$f_{\sf SW}$	0	_	15 ²⁾	kHz		
Delay time 3)	$t_{\sf d}$	_	13	-	μs		
Count Signal Delay	t_{dc}	50	200	1000	ns		
Output jitter 4)	$t_{\rm QJ}$	_	1	-	μS _{RMS}	Typ. value for square- wave signal 1 kHz	
Repeatability of magnetic thresholds 5)	B_{REP}	_	40	-	μT_{RMS}	Typ. value for $\Delta B/\Delta t > 12 \text{ mT/ms}$	
Power-on time 6)	t_{PON}	_	13	_	μs	$V_{\rm S} \ge 2.7 \ { m V}$	
Distance of hall plates	d_{HALL}	_	1.45	_	mm		
Thermal resistance 7)	R_{thJA}		-	-190	K/W	PG-SSO-4-1	

¹⁾ over operating range, unless otherwise specified. Typical values correspond to $V_{\rm S}$ = 12 V and $T_{\rm A}$ = 25°C

²⁾ To operate the sensor at the max. switching frequency, the magnetic signal amplitude must be 1.4 times higher than for static fields. This is due to the -3 dB corner frequency of the low pass filter in the signal path.

³⁾ Systematic delay between magnetic threshold reached and output switching

⁴⁾ Jitter is the unpredictable deviation of the output switching delay

⁵⁾ B_{REP} is equivalent to the noise constant

⁶⁾ Time from applying $V_{\rm S} \ge$ 2.7 V to the sensor until the output state is valid

⁷⁾ Thermal resistance from junction to ambient



Electrical and Magnetic Parameters

Calculation of the ambient temperature:

e.g. for $V_{\rm S}$ = 12.0 V, $I_{\rm Styp}$ = 5.5 mA, $V_{\rm QSATtyp}$ = 0.3 V and 2 x $I_{\rm Q}$ = 10 mA :

Power Dissipation: P_{DIS} = 72.0 mW.

In $T_A = T_i - (R_{thJA} \times P_{DIS}) = 175^{\circ}C - (190 \text{ K/W} \times 0.072 \text{ W})$

Resulting max. ambient temperature: T_A = 161.3°C

Table 6 Magnetic Characteristics 1).

Parameter	Symbol	<i>T</i> _j [°C]	Limit Values			Unit	Conditions
			min.	typ.	max.		
Operate point	B_{OP}	-40 25 150	5.2 5.0 4.7	7.7 7.5 7.1	10.3 10.0 9.5	mT	
Release point	B_{RP}	-40 25 150	-10.3 -10.0 -9.5	-7.7 -7.5 -7.1	-5.2 -5.0 -4.7	mT	
Hysteresis	B_{HYS}	-40 25 150	_ 10.0 _	- 15.0 -	_ 20.0 _	mT	
Magnetic matching	B_{MATCH}	-40 25 150	- -2.0 -	_ 0 _	_ 2.0 _	mT	Valid for B_{OP1} - B_{OP2} and B_{RP1} - B_{RP2}
Magnetic offset	B_{OFF}	-40 25 150	- -2.0 -	_ 0 _	- 2.0 -	mT	$(B_{OP} + B_{RP})/2$
Temperature compensation of magnetic thresholds	TC	_	_	-350	_	ppm/°C	

¹⁾ over operating range, unless otherwise specified. Typical values correspond to $V_{\rm S}$ = 12 V

Note: Typical characteristics specify mean values expected over the production spread.

Field Direction Definition

Positive magnetic fields related with south pole of magnet to the branded side of package.

Data Sheet 11 V 2.0, 2009-02



Timing Diagrams for the Speed and Direction Outputs

6 Timing Diagrams for the Speed and Direction Outputs

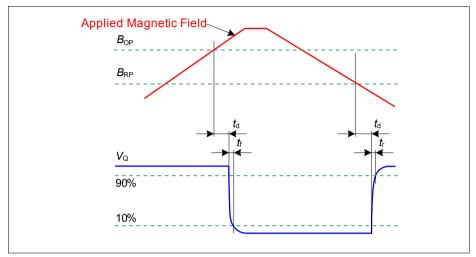


Figure 3 Timing Definition of the Speed Signal

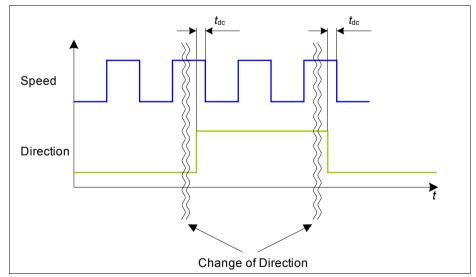


Figure 4 Timing Definition of the Direction Signal



Timing Diagrams for the Speed and Direction Outputs

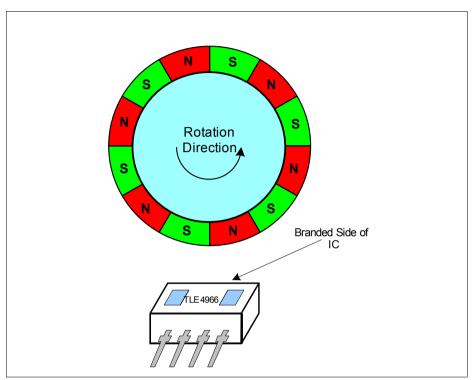


Figure 5 Definition of the Direction Signal

Rotation Direction	State of Direction Output V_{Q1}				
Left to right	Low				
Right to left	High				



Package Information

7 Package Information

7.1 Package Marking

Figure 6 Marking PG-SSO-4-1

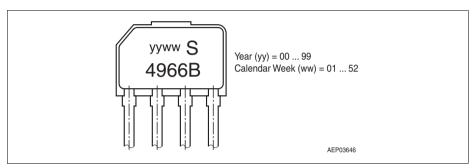


Figure 7 Marking

7.2 Distance between Chip and Package Surface

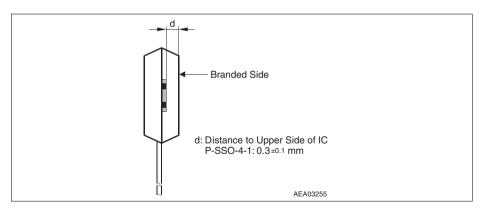


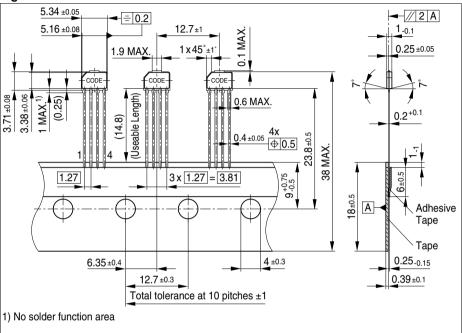
Figure 8 Distance Chip to Upper Side of IC



Package Information

7.3 Package Outlines

Figure 9 PG-SSO-4-1



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